

### NCE P-Channel Enhancement Mode Power MOSFET

### **Description**

The NCE3407AY uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , This device is suitable for use as a load switch or in PWM applications.

### **General Features**

•  $V_{DS} = -30V, I_{D} = -4.3A$ 

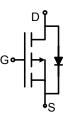
 $R_{DS(ON)}$  < 90m $\Omega$  @  $V_{GS}$ =-4.5V

 $R_{DS(ON)}$  <52m $\Omega$  @  $V_{GS}$ =-10V

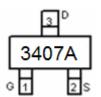
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

### **Application**

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT-23-3L top view

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3407A	NCE3407AY	SOT23-3L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T<sub>A</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	-4.3	Α
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	-20	Α
Maximum Power Dissipation	P <sub>D</sub>	1.5	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 150	$^{\circ}$ C

### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	84	°C/W
,			

### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30	-33	-	٧
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V,V <sub>GS</sub> =0V	-	-	-1	μΑ



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# NCE3407AY

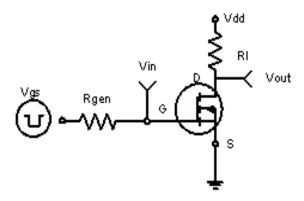
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-1	-1.5	-3	V
Drain Course On State Resistance	Б	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4 A	-	40	52	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	-	48	90	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-1A	-	10	-	S
Dynamic Characteristics (Note4)			•	•		•
Input Capacitance	C <sub>lss</sub>	\/ 45\/\/ O\/	-	700	-	PF
Output Capacitance	C <sub>oss</sub>	- V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V, - F=1.0MHz	-	120	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UWITZ	-	75	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	9	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =-15V,R <sub>L</sub> =3.6Ω	-	5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10 $V$ , $R_{GEN}$ =3 $\Omega$	-	28	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	13.5	-	nS
Total Gate Charge	Qg		-	14	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V,I <sub>D</sub> =-4A,V <sub>GS</sub> =-10V	-	3.1	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3	-	nC
Drain-Source Diode Characteristics	•		•	•		•
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =-4.3A	-	-	-1.2	V

### Notes:

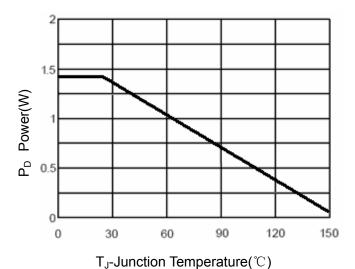
- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



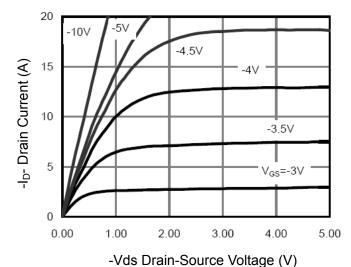
# **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



**Figure 3 Power Dissipation** 



**Figure 5 Output Characteristics** 

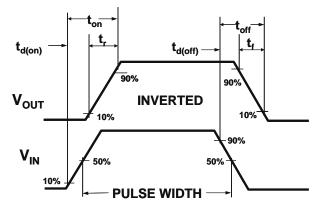
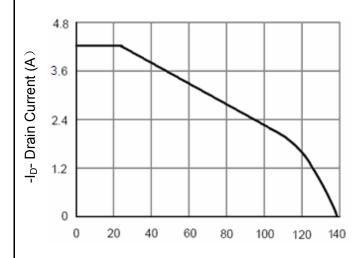


Figure 2:Switching Waveforms



T<sub>J</sub>-Junction Temperature(°C)

Figure 4 Drain Current

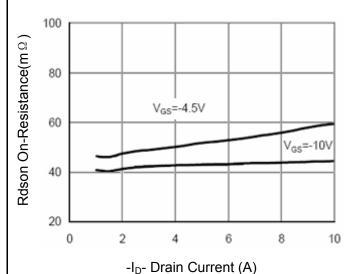
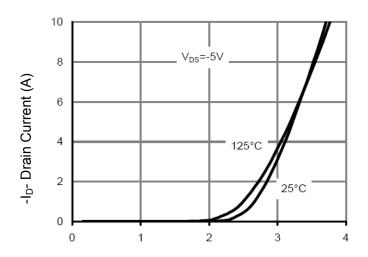
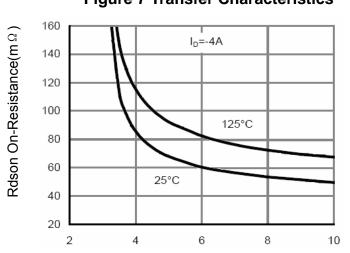


Figure 6 Drain-Source On-Resistance





-Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



-Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

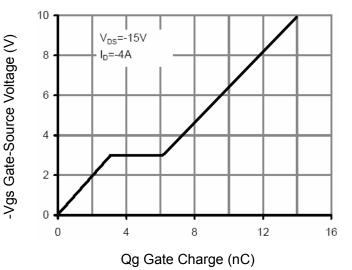


Figure 11 Gate Charge

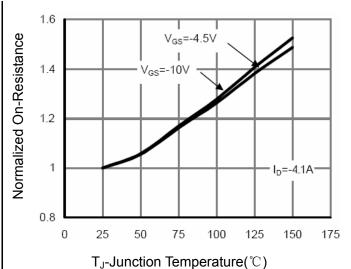


Figure 8 Drain-Source On-Resistance

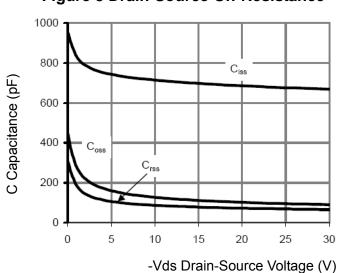


Figure 10 Capacitance vs Vds

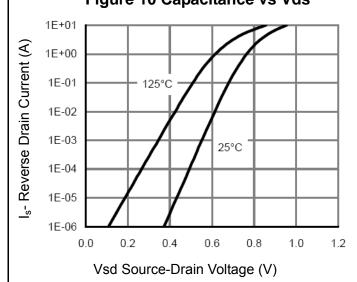
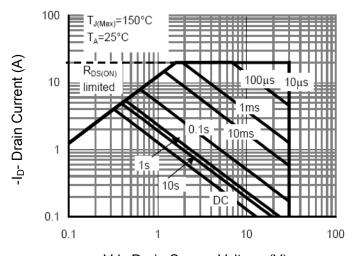


Figure 12 Source- Drain Diode Forward





**Pb Free Product** 



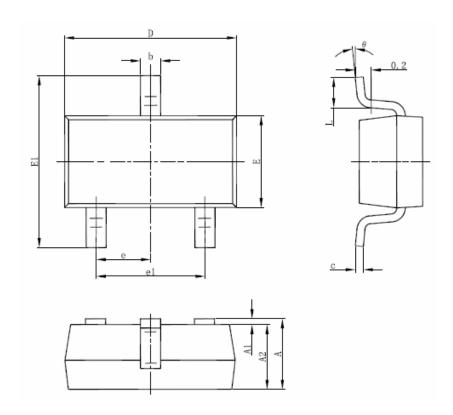
-Vds Drain-Source Voltage (V)

**Figure 13 Safe Operation Area** Transient Thermal Impedance In descending order r(t), Normalized Effective  $T_{J,PK} = T_A + P_{DM} \cdot Z_{\theta JA} \cdot R_{\theta JA}$ D=0.5, 0.3, 0.1, 0.05, 0.02, 0.01, single pulse R<sub>eJA</sub>=84°C/W Single Pulse 0.01 0.001 0.01 0.1 10 100 1000 0.00001 0.0001 Square Wave Pluse Duration(sec)

**Figure 14 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23-3L Package Information**



Symbol	Dimensions Ir	Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
e	0.950	(BSC)	0.037(	BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

### **Notes**

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact



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